

Product data sheet

1. General description

Hyperfast power diode in a SOT404 (D2PAK) surface-mountable plastic package.

2. Features and benefits

- Fast switching
- Surface-mountable package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 130 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	8	A
Static charact	eristics						
V _F	forward voltage	I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
Dynamic characteristics							
t _{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 200 A/µs; T _j = 25 °C; <u>Fig. 7</u>		-	12	18	ns





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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	no connection	mb	К—Ң—А
2	К	cathode[1]		001aaa020
3	А	anode	i	
mb	К	mounting base; connected to cathode	D2PAK (SOT404)	

[1] It is not possible to connect to pin 2 of the SOT404 package.

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BYC8B-600P	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC8B-600P	BYC8B-600P

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 130 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 130 °C; square-wave pulse	-	16	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	91	A
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Symbol	Parameter	Conditions	Min	Мах	Unit
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	100	A
T _{stg}	storage temperature		-65	175	°C
Тj	junction temperature		-	175	°C

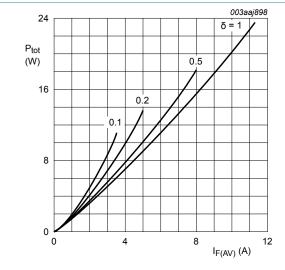
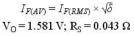
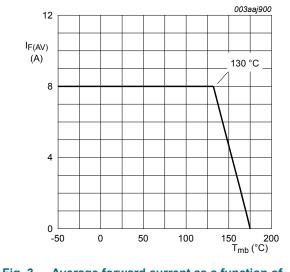


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values







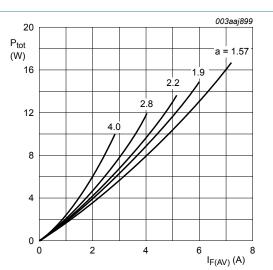
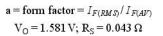
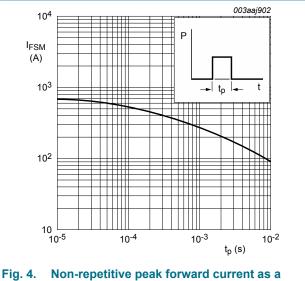


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



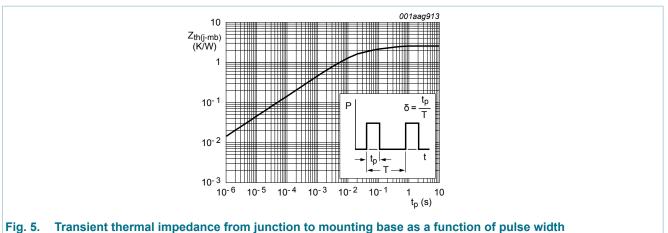


function of pulse width; square waveform; maximum values

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9. Thermal characteristics

Table 6. 1	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



rig. o. Transient themai impedance from junction to mounting base as a function of part

10. Characteristics

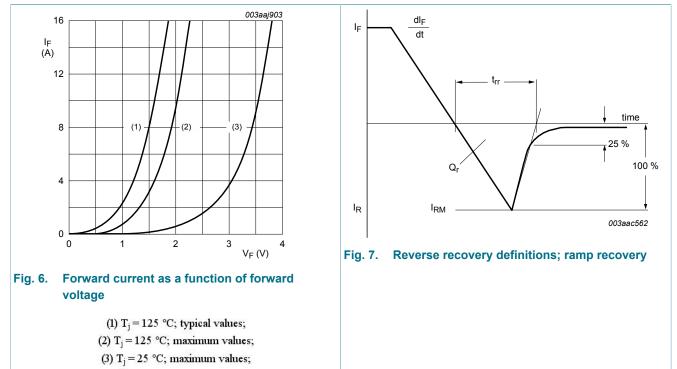
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·				
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.4	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C		μA		
		V _R = 600 V; T _j = 125 °C	-	-	200	μA
Dynamic cl	naracteristics		I			
Q _r recovered charge	recovered charge	I _F = 8 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	17	-	nC
		I _F = 8 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-	90	-	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _i = 25 °C; <u>Fig. 7</u>	-	12	18	ns

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
		$I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; \text{ d}I_{F}/\text{d}t = 500 \text{ A}/\mu\text{s}; T_{j} = 25 \text{ °C}; Fig. 7$	-	19	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	A
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	6	A

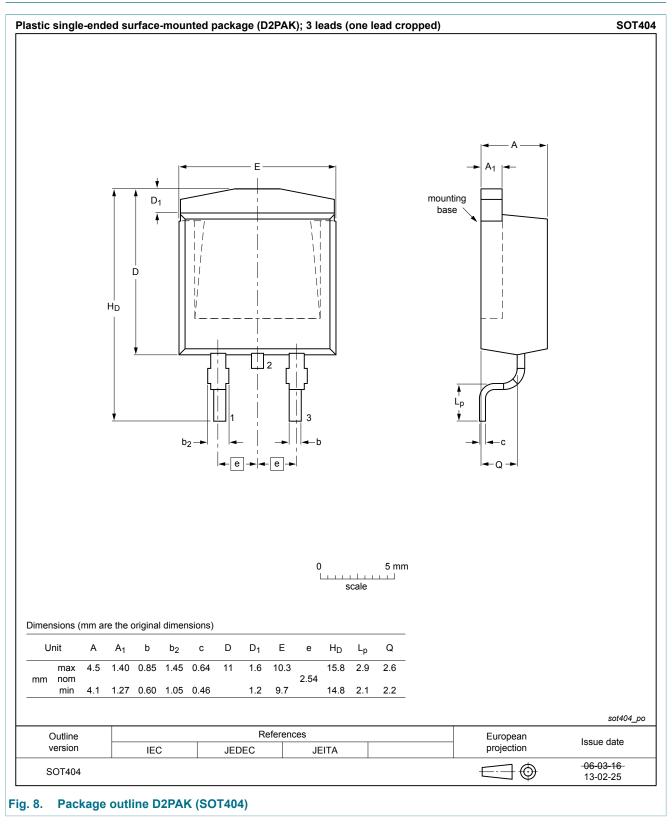


 $V_0 = 1.581 \text{ V}; \text{ R}_S = 0.043 \Omega$



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11. Package outline



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Product data sheet

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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